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Switch-mode Power Rectifier

Features and Benefits

- Center-Tap Configuration
- Low Forward Voltage
- Low Power Loss / High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 15 A Total (7.5 A Per Diode Leg)
- These Devices are Pb-Free and are RoHS Compliant*

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

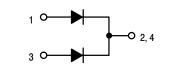
- Case: Epoxy, Molded
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model = 3B Machine Model = C

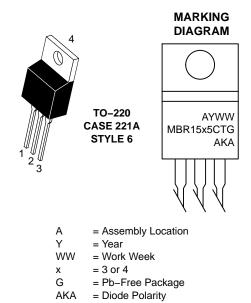


ON Semiconductor®

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SCHOTTKY BARRIER RECTIFIERS 15 AMPERES 35 and 45 VOLTS





ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|--|-------------|------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MBR1535CT MBR1545CT | V _{RRM} V _{RWM} V _R | 35 45 | V |
| Average Rectified Forward Current $(T_C = 163^{\circ}C)$ Per DiodePer Device | I _{F(AV)} | 7.5 15 | A |
| Peak Repetitive Forward Current (Square Wave, 20 kHz, T _C = 161°C) Per Diode | I _{FRM} | 15 | A |
| Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz) | I _{FSM} | 150 | A |
| Peak Repetitive Reverse Surge Current (2.0 µs, 1.0 kHz) | I _{RRM} | 1.0 | А |
| Storage Temperature Range | T _{stg} | -65 to +175 | °C |
| Operating Junction Temperature (Note 1) | TJ | -65 to +175 | °C |
| Voltage Rate of Change (Rated V _R) | dv/dt | 1000 | V/μs |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS PER DIODE

| Characteristic | Symcbol | Value | Unit |
|--|-----------------------|-------|------|
| Maximum Thermal Resistance, Junction-to-Case (Min. Pad) | $R_{	extsf{	heta}JC}$ | 3.0 | °C/W |
| Maximum Thermal Resistance, Junction-to-Ambient (Min. Pad) | R_{\thetaJA} | 60 | °C/W |

ELECTRICAL CHARACTERISTICS PER DIODE

| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|----------------|-------------|----------------------|----------------------|------|
| $\begin{array}{l} \mbox{Maximum Instantaneous Forward Voltage (Note 2)} \\ (i_F = 7.5 \mbox{ Amps, } T_J = 125^{\circ}\mbox{C}) \\ (i_F = 15 \mbox{ Amps, } T_J = 125^{\circ}\mbox{C}) \\ (i_F = 15 \mbox{ Amps, } T_J = 25^{\circ}\mbox{C}) \end{array}$ | VF | - - - | 0.47 0.63 0.66 | 0.57 0.72 0.84 | V |
| Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_J = 125^{\circ}C$) (Rated DC Voltage, $T_J = 25^{\circ}C$) | i _R | | 10 0.025 | 15 0.1 | mA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width = $300 \ \mu$ s, Duty Cycle $\leq 2.0\%$

ORDERING INFORMATION

| Device | Package | Shipping |
|------------|---------------------|-----------------|
| MBR1535CTG | TO-220 (Pb-Free) | 50 Units / Rail |
| MBR1545CTG | TO-220 (Pb-Free) | 50 Units / Rail |



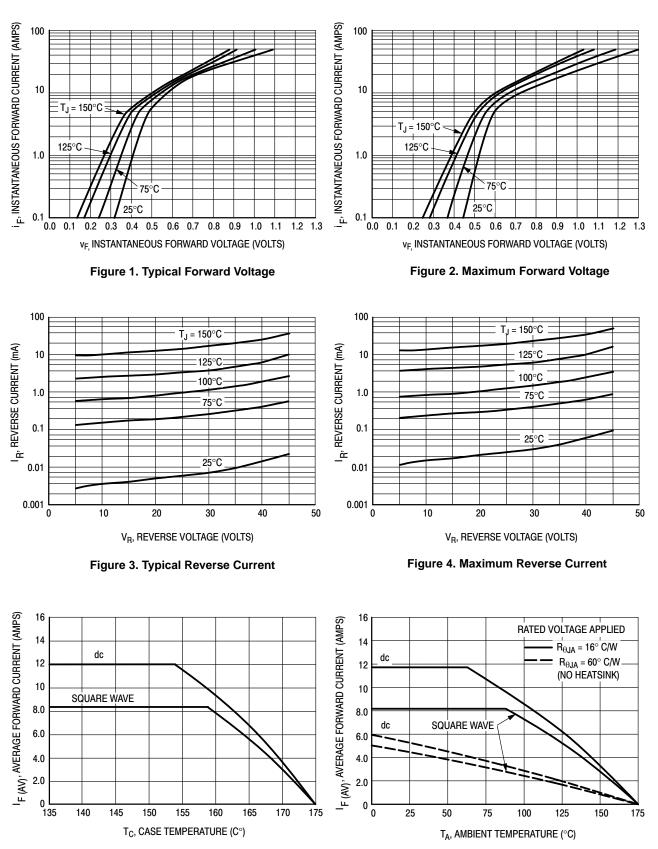




Figure 6. Current Derating, Ambient Per Leg



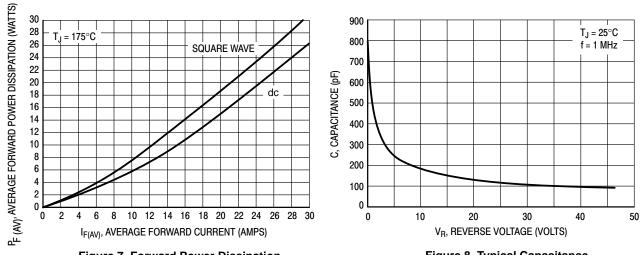


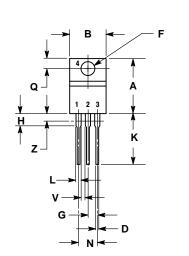
Figure 7. Forward Power Dissipation

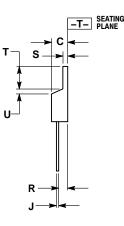
Figure 8. Typical Capacitance



PACKAGE DIMENSIONS







NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. DIMENSION Z DEFINES A ZONE WHERE ALL

BODY AND LEAD IRREGULARITIES ARE

| | INCHES | | MILLIM | IETERS |
|-----|--------|-------|--------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.570 | 0.620 | 14.48 | 15.75 |
| В | 0.380 | 0.415 | 9.66 | 10.53 |
| С | 0.160 | 0.190 | 4.07 | 4.83 |
| D | 0.025 | 0.038 | 0.64 | 0.96 |
| F | 0.142 | 0.161 | 3.61 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| н | 0.110 | 0.161 | 2.80 | 4.10 |
| ſ | 0.014 | 0.024 | 0.36 | 0.61 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| Г | 0.045 | 0.060 | 1.15 | 1.52 |
| Ν | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| Т | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| ۷ | 0.045 | | 1.15 | |
| Z | | 0.080 | | 2.04 |

STYLE 6: PIN 1 ANODE CATHODE 2. 3. ANODE CATHODE

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MBR1535CT/D